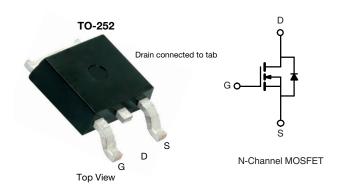


www.vishay.com

Vishay Siliconix

Automotive N-Channel 300 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | |
|---|--------|--|--|--|
| V _{DS} (V) | 300 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.330 | | | |
| I _D (A) | 10 | | | |
| Configuration | Single | | | |



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE

| ORDERING INFORMATION | | | |
|---------------------------------|-------------------|--|--|
| Package | TO-252 | | |
| Lead (Pb)-free and Halogen-free | SQD10N30-330H-GE3 | | |

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | |
|---|-------------------------|-----------------------------------|-------------|----|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Drain-Source Voltage | V_{DS} | 300 | V | | |
| Gate-Source Voltage | V_{GS} | ± 30 | V | | |
| Continuous Drain Current | T _C = 25 °C | - I _D | 10 | | |
| Continuous Diain Current | T _C = 125 °C | | 5 | | |
| Continuous Source Current (Diode Conduction) a | I_S | 50 | Α | | |
| Pulsed Drain Current ^b | I _{DM} | 16 | | | |
| Single Pulse Avalanche Current ^e | L = 0.05 mH | I _{AS} | 12.65 | | |
| Single Pulse Avalanche Energy e | L = 0.03 IIII | E _{AS} | 4 | mJ | |
| Maximum Power Dissipation ^b | T _C = 25 °C | T _C = 25 °C | 107 | W | |
| iviaximum Fower Dissipation 5 | T _C = 125 °C | P_{D} | 35 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|-------------|-------------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-Ambient F | PCB Mount c | R_{thJA} | 50 | °C/W | |
| Junction-to-Case (Drain) | | R _{thJC} | 1.4 | C/VV | |

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. $1.5 \text{ k}\Omega$ resistance in series with the gate.



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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT | |
|--------------------------------------|--------------------------|--|--|------|-------|-------|------|--|
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | | 300 | - | - | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | | 3.8 | 4.4 | V | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 30 \text{ V}$ | | - | ± 100 | nA | |
| | | V _{GS} = 0 V | V _{DS} = 300 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 300 V, T _J = 125 °C | - | - | 50 | μΑ | |
| | | $V_{GS} = 0 V$ | $V_{DS} = 300 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$ | - | - | 250 | | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 10 | - | - | Α | |
| | | V _{GS} = 10 V | I _D = 14 A | - | 0.275 | 0.330 | Ω | |
| Drain-Source On-State Resistance a | R _{DS(on)} | V _{GS} = 10 V | I _D = 14 A, T _J = 125 °C | - | - | 0.733 | | |
| | | V _{GS} = 10 V | I _D = 14 A, T _J = 175 °C | - | - | 1.000 | | |
| Forward Transconductance b | 9 _{fs} | $V_{DS} = 15 \text{ V}, I_D = 14 \text{ A}$ | | - | 26 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 1749 | 2190 | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ | V _{DS} = 25 V, f = 1 MHz | - | 112 | 140 | | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 44 | 55 | | |
| Total Gate Charge ^c | Qg | | | - | 31 | 47 | nC | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 150 \text{ V}, I_D = 7 \text{ A}$ | - | 8 | - | | |
| Gate-Drain Charge ^c | Q _{gd} |] | | - | 9.6 | - | | |
| Gate Resistance | R _g | | f = 1 MHz | | 0.8 | 3 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | | 10 | 15 | | |
| Rise Time ^c | t _r | V_{DD} = 150 V, R_L = 21 Ω $I_D \cong 7$ A, V_{GEN} = 10 V, R_g = 1 Ω | | - | 18 | 28 | - ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 20 | 30 | | |
| Fall Time ^c | t _f | | | - | 8 | 12 | | |
| Source-Drain Diode Ratings and Chara | acteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 16 | Α | |
| Forward Voltage | V _{SD} | I _F = 25 A, V _{GS} = 0 V | | | 0.9 | 1.5 | V | |

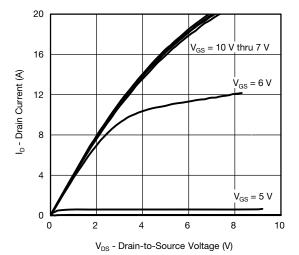
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

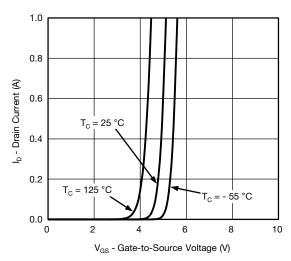
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



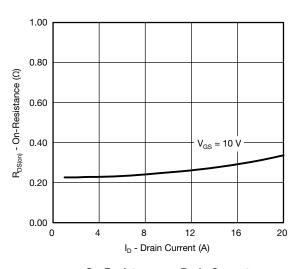
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



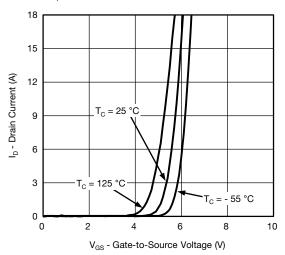
Output Characteristics



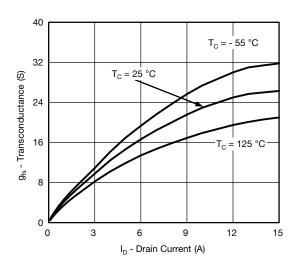
Transfer Characteristics



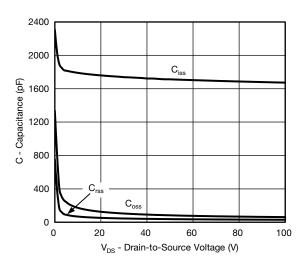
On-Resistance vs. Drain Current



Transfer Characteristics



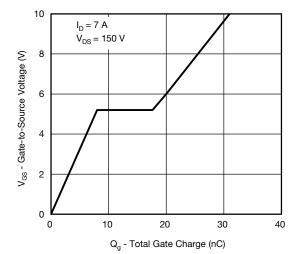
Transconductance



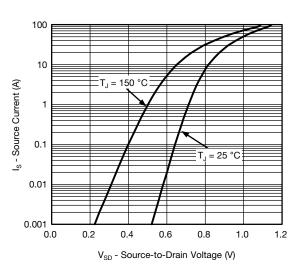
Capacitance



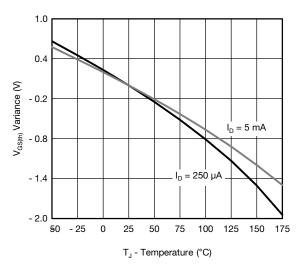
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



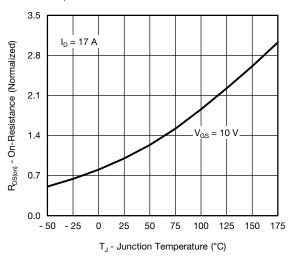
Gate Charge



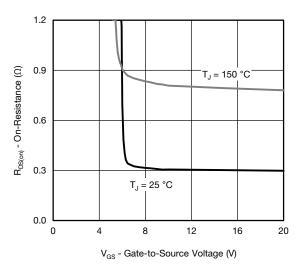
Source Drain Diode Forward Voltage



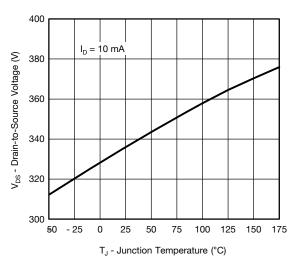
Threshold Voltage



On-Resistance vs. Junction Temperature



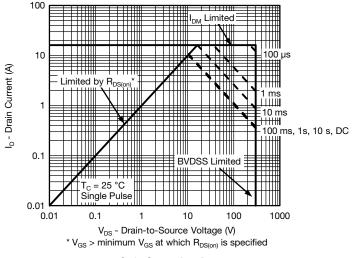
On-Resistance vs. Gate-to-Source Voltage



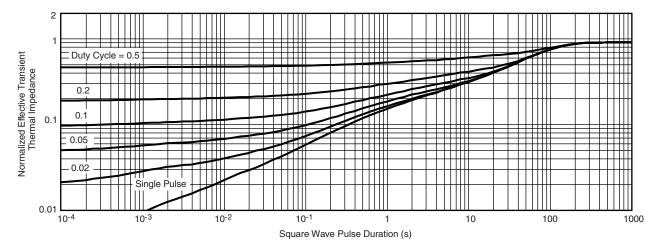
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



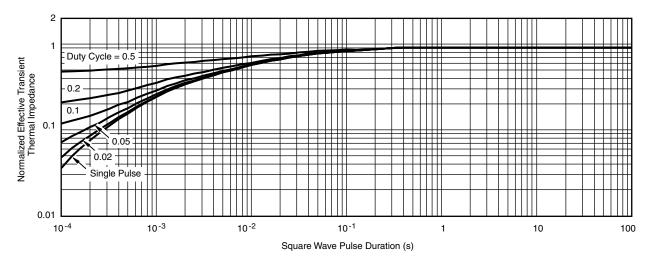
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267070.



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| REVISION HISTORY ^a | | | | | |
|-------------------------------|-------------|--|--|--|--|
| REVISION | DATE | DESCRIPTION OF CHANGE | | | |
| В | 26-Feb-2015 | UIS changed | | | |
| С | 04-May-2015 | R _g , C _{iss} and t _r updated | | | |

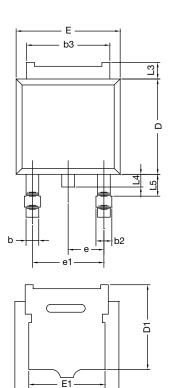
Note

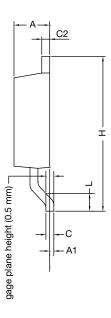
a. As of April 2014



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TO-252AA Case Outline





| | MILLIN | IETERS | INCHES | | |
|--|----------|--------|-----------|-------|--|
| DIM. | MIN. | MAX. | MIN. | MAX. | |
| Α | 2.18 | 2.38 | 0.086 | 0.094 | |
| A1 | - | 0.127 | - | 0.005 | |
| b | 0.64 | 0.88 | 0.025 | 0.035 | |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 | |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 | |
| С | 0.46 | 0.61 | 0.018 | 0.024 | |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 | |
| D | 5.97 | 6.22 | 0.235 | 0.245 | |
| D1 | 4.10 | - | 0.161 | - | |
| E | 6.35 | 6.73 | 0.250 | 0.265 | |
| E1 | 4.32 | - | 0.170 | - | |
| Н | 9.40 | 10.41 | 0.370 | 0.410 | |
| е | 2.28 | BSC | BSC | | |
| e1 | 4.56 BSC | | 0.180 BSC | | |
| L | 1.40 | 1.78 | 0.055 | 0.070 | |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 | |
| L4 | - | 1.02 | - | 0.040 | |
| L5 | 1.01 | 1.52 | 0.040 | 0.060 | |
| ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019 | | | | | |

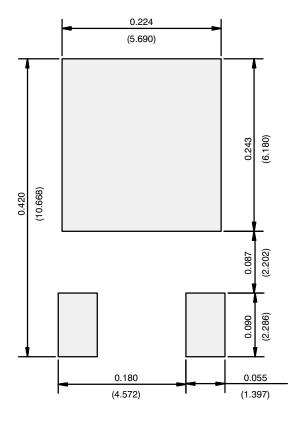
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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